

# SILICON POWER RECTIFIER

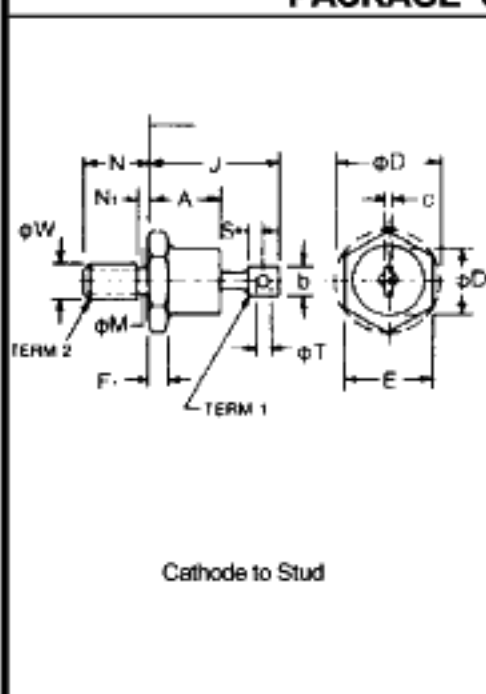
**DESCRIPTION:**

The **ASI 1N253** is Designed for General Purpose Power Supply Applications.

**MAXIMUM RATINGS**

$I_o$	1.0 A @ $T_c = 135^\circ\text{C}$
$V_{RWM}$	100 V
$T_J$	$-65^\circ\text{C}$ to $+170^\circ\text{C}$
$T_{STG}$	$-65^\circ\text{C}$ to $+175^\circ\text{C}$
$\theta_{JC}$	$35^\circ\text{C/W}$

PACKAGE STYLE DO-4				
SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A		0.405		10.28
b		0.250		6.35
c				
$\phi D$		0.505		12.82
$\phi D_1$	0.265	0.424	6.74	10.76
E	0.423	0.438	10.75	11.12
$F_1$	0.075	0.175	1.91	4.44
J	0.600	0.800	15.24	20.32
$\phi M$	0.163	0.189	4.15	4.80
N	0.422	0.453	10.72	11.50
$N_1$		0.078		1.98
S				
$\phi T$	0.060	0.095	1.53	2.41
$\phi W$	10-32	UNF-2A	10-32	UNF-2A


**CHARACTERISTICS**  $T_J = 25^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIM	UNITS
$I_R$	$V_R = 100\text{ V}$ $T_J = 150^\circ\text{C}$		10 100	100 1000	$\mu\text{A}$
$V_F$	$I_F = 1.0\text{ A}$			1.2	V
$I_{FSM}$	NON REPETITIVE $t_p = 8.3\text{ mS}$	15			A